FJPF2145
ESBC™ Rated NPN Power Transistor

ESBC Features (FDC655 MOSFET)

$V_{CS(ON)}$	I_C	Equiv. $R_{CS(ON)}$ (1)
0.21 V	2 A	0.105 Ω

- Low Equivalent On Resistance
- Very Fast Switch: 150 kHz
- Wide RBSOA: Up to 1100 V
- Avalanche Rated
- Low Driving Capacitance, no Miller Capacitance
- Low Switching Losses
- Reliable HV Switch: No False Triggering due to High dv/dt Transients

Applications

- High-Voltage, High-Speed Power Switches
- Emitter-Switched Bipolar/MOSFET Cascode (ESBC™)
- Smart Meters, Smart Breakers, SMPS, HV Industrial Power Supplies
- Motor Drivers and Ignition Drivers

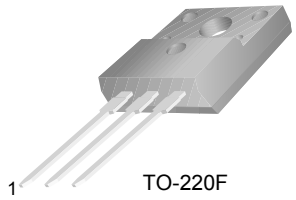
Description

The FJPF2145 is a low-cost, high-performance power switch designed to provide the best performance when used in an ESBC™ configuration in applications such as: power supplies, motor drivers, smart grid, or ignition switches. The power switch is designed to operate up to 1100 volts and up to 5 amps, while providing exceptionally low on-resistance and very low switching losses.

The ESBC™ switch can be driven using off-the-shelf power supply controllers or drivers. The ESBC™ MOSFET is a low-voltage, low-cost, surface-mount device that combines low-input capacitance and fast switching. The ESBC™ configuration further minimizes the required driving power because it does not have Miller capacitance.

The FJPF2145 provides exceptional reliability and a large operating range due to its square reverse-bias-safe-operating-area (RBSOA) and rugged design. The device is avalanche rated and has no parasitic transistors, so is not prone to static dv/dt failures.

The power switch is manufactured using a dedicated high-voltage bipolar process and is packaged in a high-voltage TO-220F package.



1.Base 2.Collector 3.Emitter

Figure 1. Pin Configuration

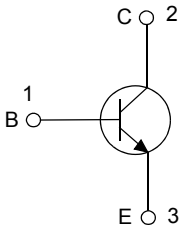


Figure 2. Internal Schematic Diagram

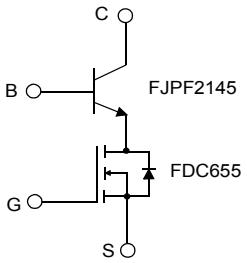


Figure 3. ESBC Configuration(2)

Ordering Information

Part Number	Marking	Package	Packing Method
FJPF2145TU	J2145	TO-220F	TUBE

Notes:

1. Figure of Merit.
2. Other Fairchild MOSFETs can be used in this ESBC application.

Absolute Maximum Ratings[3]

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at T_A = 25°C unless otherwise noted..

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	1100	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current (DC)	5	A
I_B	Base Current	1.5	A
P_C	Collector Dissipation (T_C = 25°C)	40	W
T_J	Operating and Junction Temperature Range	-55 to +125	°C
T_{STG}	Storage Temperature Range	-55 to +150	°C
EAR[4]	Avalanche Energy (T_J = 25°C, 1.2 mH)	15	mJ

Notes:

3. Pulse test is pulse width ≤ 5 ms, duty cycle ≤ 10%.
4. Lab characterization data only for reference.

Thermal Characteristics

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Max.	Units
$R_{\theta jc}$	Thermal Resistance, Junction to Case	3.125	°C/W
$R_{\theta ja}$	Thermal Resistance, Junction to Ambient	70.44	°C/W

Electrical Characteristics[5]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
BV_{CBO}	Collector-Base Breakdown Voltage	I_C = 1 mA, I_E = 0	1100			V
BV_{CEO}	Collector-Emitter Breakdown Voltage	I_C = 5 mA, I_B = 0	800			V
BV_{EBO}	Emitter-Base Breakdown Voltage	I_E = 1 mA, I_C = 0	7			V
I_{CBO}	Collector Cut-off Current	V_{CB} = 800 V, I_E = 0			10	µA
I_{EBO}	Emitter Cut-off Current	V_{EB} = 5 V, I_C = 0			10	µA
h_{FE1}	DC Current Gain	V_{CE} = 5 V, I_C = 0.2 A	20		40	
h_{FE2}		V_{CE} = 5 V, I_C = 1 A	8			
V_{CE}(sat)	Collector-Emitter Saturation Voltage	I_C = 0.25 A, I_B = 0.05 A		0.051		V
		I_C = 0.5 A, I_B = 0.167 A		0.055		V
		I_C = 1 A, I_B = 0.33 A		0.085		V
		I_C = 1.5 A, I_B = 0.3 A		0.159	2.000	V
V_{BE}(sat)	Base-Emitter Saturation Voltage	I_C = 500 mA, I_B = 50 mA		0.756		V
		I_C = 1.5 A, I_B = 0.3 A		0.840	1.500	V
		I_C = 2 A, I_B = 0.4 A		0.863		V
C_{IB}	Input Capacitance	V_{EB} = 5 V, I_C = 0, f = 1 MHz		1.618		pF
C_{OB}	Output Capacitance	V_{CB} = 200 V, I_E = 0, f = 1 MHz		11.39		pF
f_T	Current Gain Bandwidth Product	V_{CE} = 10 V, I_C = 0.2 A		15		MHz

Note:

5. Pulse test is pulse width ≤ 5 ms, duty cycle ≤ 10%.

ESBC-Configured Electrical Characteristics[6]

Values are at T_A = 25°C unless otherwise noted.

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
f_T	Current Gain Bandwidth Product	I_C = 0.1 A, V_{CE} = 10 V		28.40		MHz
It_f	Inductive Current Fall Time	V_{CC} = 100 V, V_{GS} = 10 V, R_G = 4 7Ω, V_{Clamp} = 500 V, I_C = 0.5 A, I_B = 0.05 A, H_{FE} = 10, L_C = 166 μH, SRF = 684 kHz		95		ns
t_s	Inductive Storage Time			0.13		ns
Vt_f	Inductive Voltage Fall Time			135		ns
Vt_r	Inductive Voltage Rise Time			80		ns
t_c	Inductive Crossover Time			115		ns
It_f	Inductive Current Fall Time	V_{CC} = 100 V, V_{GS} = 10 V, R_G = 47 Ω, V_{Clamp} = 500 V, I_C = 1 A, I_B = 0.2 A, H_{FE} = 5, L_C = 166 μH, SRF = 684 kHz		50		ns
t_s	Inductive Storage Time			0.34		ns
Vt_f	Inductive Voltage Fall Time			150		ns
Vt_r	Inductive Voltage Rise Time			60		ns
t_c	Inductive Crossover Time			95		ns
V_{CSW}	Maximum Collector-Source Voltage at Turn-off without Snubber	h_{FE} = 5, I_C = 2 A	1100			V
$I_{GS(OS)}$	Gate-Source Leakage Current	V_{GS} = ±20 V		1		nA
$V_{CS(ON)}$	Collector-Source On Voltage	V_{GS} = 10 V, I_C =2 A, I_B = 0.67 A, h_{FE} = 3		0.209		V
		V_{GS} = 10 V, I_C = 1 A, I_B = 0.33 A, h_{FE} = 3		0.114		V
		V_{GS} = 10 V, I_C = 0.5 A,I_B = 0.17 A, h_{FE} = 3		0.068		V
		V_{GS} = 10 V, I_C = 0.3 A, I_B = 0.06 A, h_{FE} = 5		0.062		V
$V_{GS(th)}$	Gate Threshold Voltage	V_{BS} = $V_{GS,}$ I_B = 250 μA		1.9		V
C_{iss}	Input Capacitance (V_{GS} = V_{CB} = 0)	V_{CS} = 25 V, f = 1 MHz		470		pF
$Q_{GS(tot)}$	Gate-Source Change V_{CB} = 0	V_{GS} = 10 V, I_C = 6.3 A, V_{CS} = 25 V		9		nC
$R_{DS(ON)}$	Static Drain-to-Source On Resistance	V_{GS} = 10 V, I_D = 6.3 A		21		mΩ
		V_{GS} = 4.5 V, I_D = 5.5 A		26		mΩ
		V_{GS} = 10 V, I_D = 6.3 A, T_J = 125°C		30		mΩ

Note:

6. A typical FDC655 MOSFET was used for the specifications above. Values could vary if other Fairchild MOSFETs are used.